

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	1687413	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 06:31
L7	230	L6 and (((anti reflectie) or ARC) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/28 06:31
L8	92	L6 and (((anti reflectie) or ARC) same pattern same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/28 06:32
L9	96	(((anti reflectie) or ARC) same pattern same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/28 06:33
L10	2	(((anti reflectie) or ARC) same pattern same hardmask).clm.	US-PGPUB	ADJ	ON	2006/07/28 06:33

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	("4142926") PN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:27
S2	12667	semiconductor with lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S3	24	S2 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S4	1543042	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/25 13:53
S5	43735	S4 and lithography	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 14:46
S6	93	S5 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:47
S7	0	S5 and ((thin film stack) with polysilicon with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:48
S8	0	S5 and ((thin film stack) same polysilicon same oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:49
S9	10	S5 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57

EAST Search History

S10	4	S9 and ((anti reflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/06 09:34
S11	4	S10 and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:58
S12	71	S4 and ((thin film stack) and polysilicon and oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:57
S13	15	S12 and ((anti reflectie) or ARC) and \$5mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 15:00
S14	15	S13 and etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 14:59
S15	4	S14 and (((anti reflectie) or ARC) with pattern)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:02
S16	0	S4 and (((anti reflectie) or ARC) with pattern with hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:05
S17	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:06
S18	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:08
S19	0	S4 and (((anti reflectie) or ARC) same hardmask) and ((thin film stack) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07

EAST Search History

S21	130	S4 and (((anti reflectie) or ARC) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:07
S22	64	S4 and (((anti reflectie) or ARC) same pattern same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/28 06:32
S23	0	S4 and (((anti reflectie) or ARC) same pattern same hardmask) and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:09
S24	445	S4 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S25	0	S4 and ((thin film stack) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/07/26 16:11
S26	10	S4 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/11/09 14:28
S27	1584605	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:28
S28	11	S27 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 12:22
S29	2	("20050098821").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 14:30
S30	2	S29 and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:43

EAST Search History

S31	2	S29 and hardmask and (ARC (anti adj reflect\$4 adj coating))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 14:45
S32	6126	438/257,258,241,275,689.ccls	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 12:15
S33	0	S32 and ((thin film stack) with \$5mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 12:22
S34	9	S32 and (thin film stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 12:23
S35	2	("20040043592").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/24 09:50
S36	1630090	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 09:34
S37	33256	S36 and ((anti reflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:35
S38	1630090	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 09:35
S39	46174	S38 and ((anti reflect\$4) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/06 09:37
S40	479	S39 and (hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/06 09:42

EAST Search History

S41	6	S40 and (thin with film with stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/06 09:49
S42	1636228	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/23 14:35
S43	33545	S42 and ((antireflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:36
S44	33545	S42 and ((anti reflectie) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:38
S46	43	S42 and (((anti reflectie) or ARC) with hardmask with material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/23 14:46
S47	67	S42 and (((anti reflective) or ARC) with hardmask with material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:51
S48	2	("20050098821").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 15:12
S49	2	("20040043592").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/24 09:50
S50	0	S49 and (((anti reflective) or ARC) with hardmask with material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:51
S51	0	S49 and (((anti reflective) or ARC) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:53

EAST Search History

S52	1	S49 and ((anti reflective) or ARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:52
S53	0	S49 and ((anti reflective) or ARC) and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 09:54
S54	0	S49 and hardmask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 10:19
S55	2	("20050208434").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/24 10:20
S56	1636228	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/24 12:13
S57	162	S56 and (((anti reflective) or ARC) with hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 12:45
S58	8	S57 and (flash memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 12:45
S59	2	("20050067663").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/24 12:31
S62	200	S56 and (((anti reflective) or ARC) same hardmask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/24 12:45
S63	10	S62 and (flash memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 13:53

EAST Search History

S64	1636228	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/25 13:53
S65	36876	S64 and (flash memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 13:54
S66	15	S64 and (flash memory gate stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 14:22
S67	388	S64 and ((applied materials\$4 advanced patterning film\$4) or APF\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 14:24
S68	1	S64 and (((applied materials\$4 advanced patterning film\$4) or APF\$4) with (hard mask))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 14:30
S69	17	S64 and (((applied materials\$4 advanced patterning film\$4) or APF\$4) same (hard mask))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/25 14:31
S70	119	(gate with stack) and (hard adj mask) and ARC and pattern\$3 and (etch\$3 with stack)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 15:16
S71	17	(gate with stack) and (hard adj mask) and ARC and pattern\$3 and (etch\$3 with stack) and (amorphous adj carbon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/31 15:17